

Abstracts

V-Band Double-Drift Read Silicon IMPATTs

Y.E. Ma, E.M. Nakaji and W.F. Thrower. "V-Band Double-Drift Read Silicon IMPATTs." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 167-168.

Double-drift hybrid Read silicon IMPATTs have been fabricated in the millimeter-wave frequency range with RF performance superior to that of more conventional double-drift flat diodes. State-of-the-art output power of 2.15 W was obtained at 60 GHz with 8.8 percent efficiency. The best DC-to-RF conversion efficiency achieved was 12 percent.

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